

## Single High Side Switch

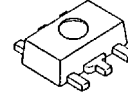
### ■ GENERAL DESCRIPTION

The NJW4830 is the single high-side switch that can supply 0.5A.

The active clamp circuit, overcurrent and thermal shutdown are built-in with Pch MOS FET.

It can be controlled by a logic signal (3V/5V) directly. Therefore, it is suitable for Car accessory, Industrial Equipments and other applications.

### ■ PACKAGE OUTLINE

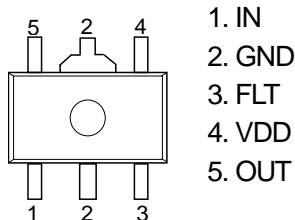


NJW4830U2

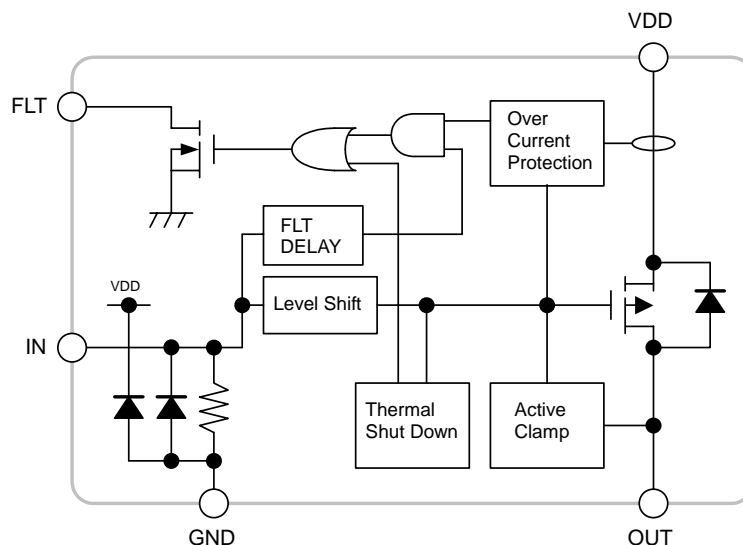
### ■ FEATURES

- Drain-Source Voltage                    45V
- Drain Current                                0.5A
- Corresponding with Logic Voltage Operation: 3V/5V
- Low On-Resistance                        0.35Ω (typ.)
- Low Consumption Current                110μA (typ.)
- Active Clamp Circuit
- Over Current Protection
- Thermal Shutdown
- Package Outline                            SOT89-5

### ■ PIN CONFIGURATION



### ■ BLOCK DIAGRAM



# NJW4830

## ■ ABSOLUTE MAXIMUM RATINGS

(Ta=25°C)

PARAMETER	SYMBOL	RATINGS	UNIT	REMARK
Drain-Source Voltage	V <sub>DS</sub>	+45	V	VDD-OUT Pin
Supply Voltage	V <sub>DD</sub>	+45	V	VDD-GND Pin
Input Voltage	V <sub>IN</sub>	-0.3 to +6	V	IN-GND Pin
FLT Pin Voltage	V <sub>FLT</sub>	-0.3 to +6	V	FLT-GND Pin
Power Dissipation	P <sub>D</sub>	625 (*1) 2,400 (*2)	mW	-
Active Clamp Tolerance (Single Pulse)	E <sub>AS</sub>	10	mJ	-
Active Clamp Current	I <sub>AP</sub>	0.5	A	-
Junction Temperature	T <sub>j</sub>	-40 to +150	°C	-
Operating Temperature	T <sub>opr</sub>	-40 to +85	°C	-
Storage Temperature	T <sub>stg</sub>	-50 to +150	°C	-

(\*1): Mounted on glass epoxy board. (76.2 × 114.3 × 1.6mm:based on EIA/JDEC standard size, 2Layers, Cu area 100mm<sup>2</sup>)

(\*2): Mounted on glass epoxy board. (76.2 × 114.3 × 1.6mm:based on EIA/JDEC standard, 4Layers)

(For 4Layers: Applying 74.2 × 74.2mm inner Cu area and a thermal via hall to a board based on JEDEC standard JESD51-5)

## ■ RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	REMARK
Drain-Source Voltage	V <sub>DS</sub>	0	-	40	V	VDD-OUT Pin
Supply Voltage	V <sub>DD</sub>	4.6	-	40	V	VDD-GND Pin
Output Current	I <sub>O</sub>	0	-	0.5	A	VDD-OUT Pin
Input Pin Voltage	V <sub>IN</sub>	0	-	5.5	V	IN-GND Pin
FLT Pin Voltage	V <sub>FLT</sub>	0	-	5.5	V	FLT-GND Pin

## ■ ELECTRICAL CHARACTERISTICS

(Unless otherwise noted,  $V_{DS}=13V$ ,  $T_a=25^{\circ}C$ )

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain-Source Output Clamp Voltage	$V_{DSS\_CL}$	$V_{IN}=0V$ , $I_O=1mA$ , $V_{DD}=40V$	$V_{DD}-45$	–	–	V
High Level Input Voltage	$V_{IH}$	$I_O=10mA$	2.64	–	–	V
Low Level Input Voltage	$V_{IL}$	$I_O=100\mu A$	–	–	0.9	V
Protection Circuit Function Input Voltage Range	$V_{IN\_opr}$		2.64	–	5.5	V
OUT Pin Leak Current at OFF State	$I_{OLEAKOUT}$	$V_{IN}=0V$ , $V_{DD}=40V$	–	–	1	$\mu A$
Quiescent Current 1	$I_{DD1}$	$V_{IN}=0V$ , $V_{DD}=40V$	–	–	1	$\mu A$
Quiescent Current 2	$I_{DD2}$	$V_{IN}=5V$	–	110	150	$\mu A$
Input Current	$I_{IN}$	$V_{IN}=5V$	–	150	190	$\mu A$
On-state Resistance	$R_{DS\_ON}$	$V_{IN}=5V$ , $I_O=0.5A$	–	0.35	0.6	$\Omega$
Over Current Protection1	$I_{LIMIT1}$	$V_{IN}=5V$ , $V_{DS}=5V$	0.5	0.75	1.2	A
Over Current Protection2	$I_{LIMIT2}$	$V_{IN}=5V$ , $V_{DD}=V_{DS}=40V$	0.1	0.4	–	A
Turn-on Time	$t_{ON}$	$V_{IN}=0$ to $5V$ , $I_O=0.5A$	–	20	–	$\mu s$
Turn-off Time	$t_{OFF}$	$V_{IN}=5$ to $0V$ , $I_O=0.5A$	–	20	–	$\mu s$
OUT–VDD Voltage Difference	$V_{PDOV}$	$V_{IN}=0V$ , $I_{ORH}=1A$	–	0.85	1.2	V
FLT Pin Low Level Output Voltage	$V_{VFLT}$	$I_{FLT}=500\mu A$	–	0.25	0.5	V
FLT Pin Leak Current at High Level	$I_{OLEAKFLT}$	$V_{FLT}=5.5V$	–	–	1	$\mu A$
FLT Delay Time	$t_{DFLT}$	$V_{IN}=0$ to $5V$ , $V_{DS}=22V$	–	5	–	ms

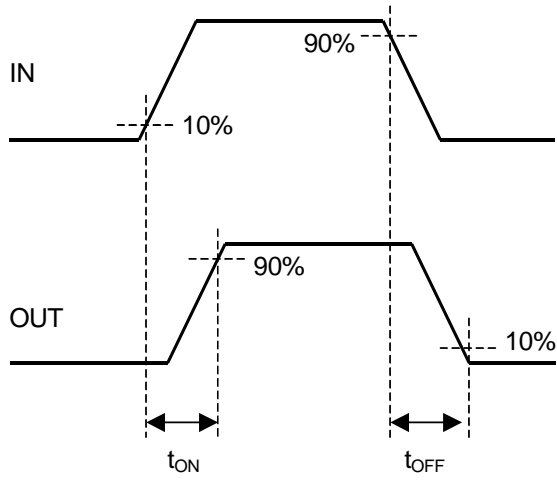
## ■ TRUTH TABLE

Input Signal	Operating Condition	FLT Pin	Output Status
L	Normal	H	OFF
H		L	ON
L	Over Current $I_{LIMIT1}$	H	OFF
H		L	$I_{LIMIT1}$
L	Over Current $I_{LIMIT2}$	H	OFF
H		L	$I_{LIMIT2}$
L	$T_j > 150^{\circ}C$	H	OFF
H		H	OFF

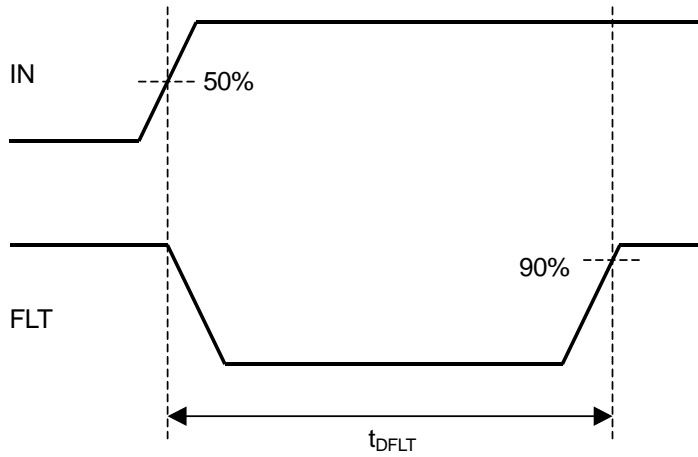
# NJW4830

## ■ TIMING CHART

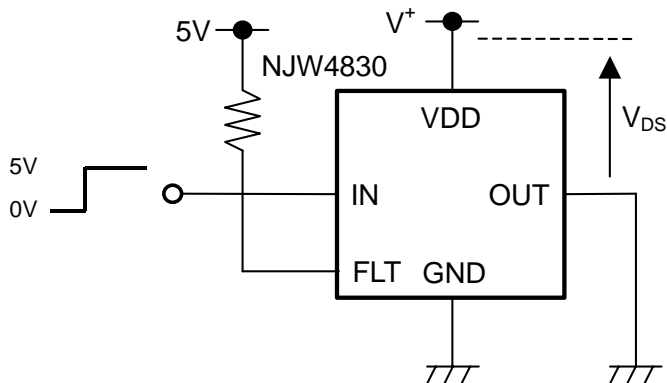
ON, OFF Switching Time ( $V_{IN}=0$  to  $5V$ ,  $V_{DD}=13V$ ,  $I_O=0.5A$ )

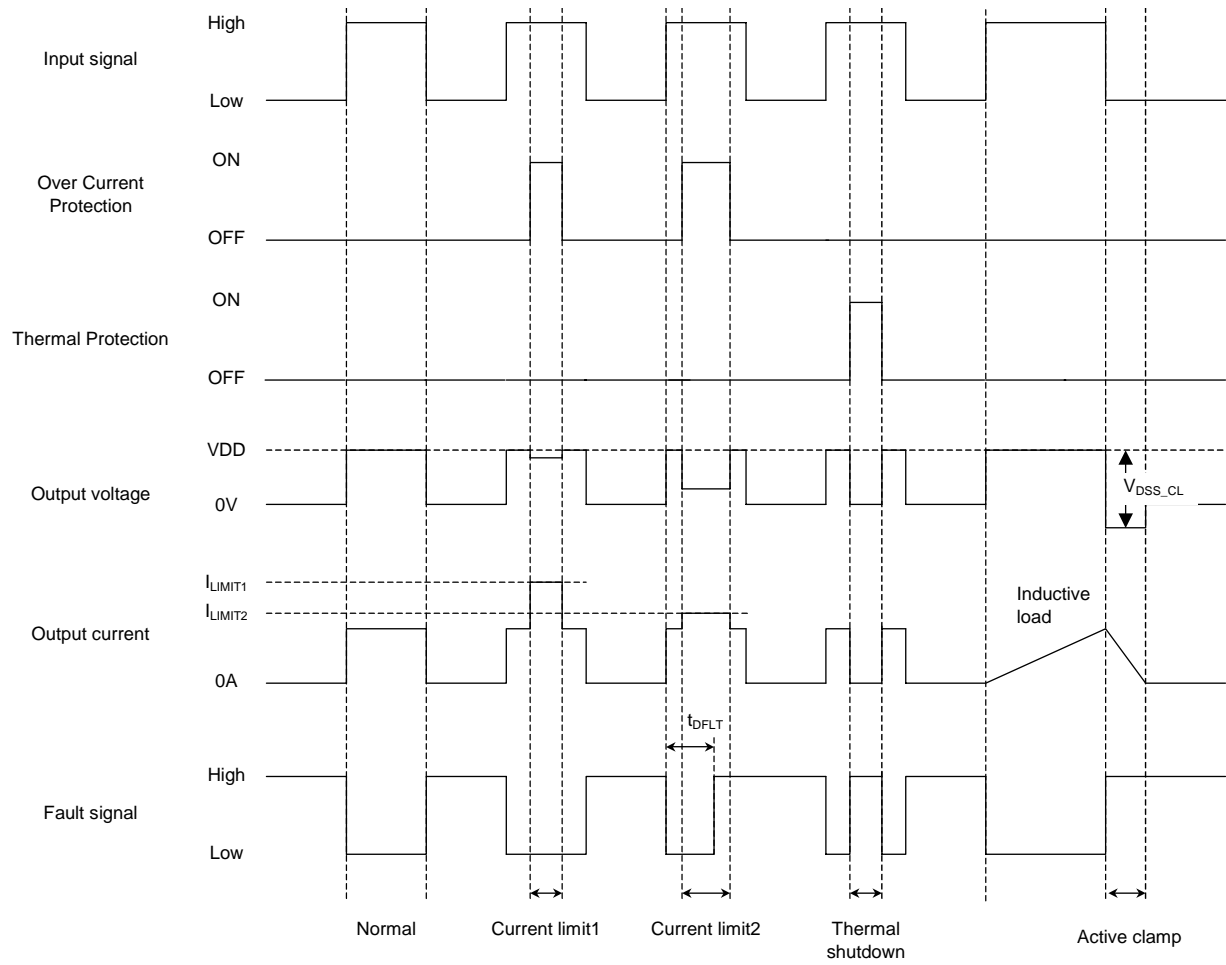


FLT Delay Time ( $V_{IN}=0$  to  $5V$ ,  $V_{DD}=V_{DS}=22V$ )

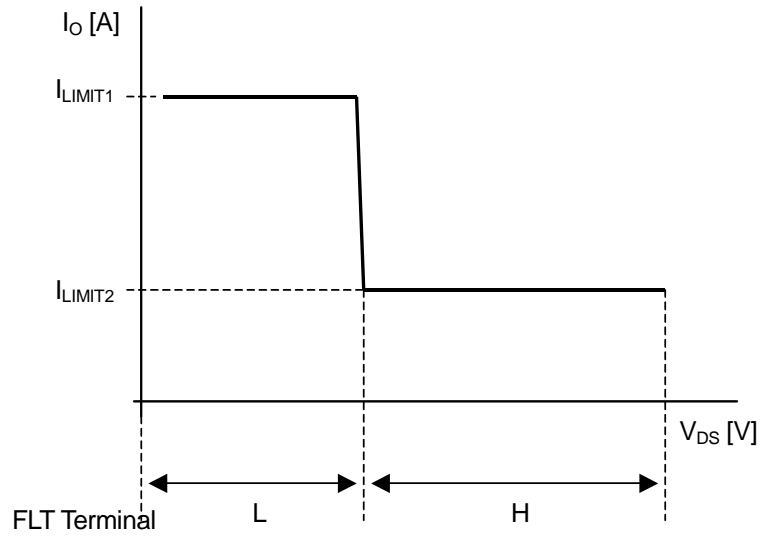


FLT Delay Time Measurement Circuit

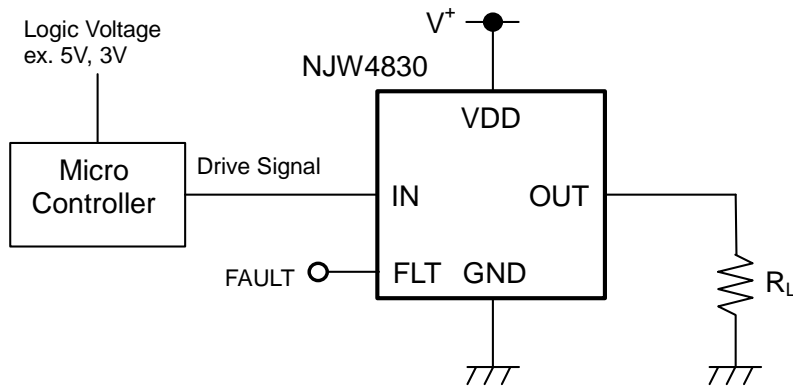




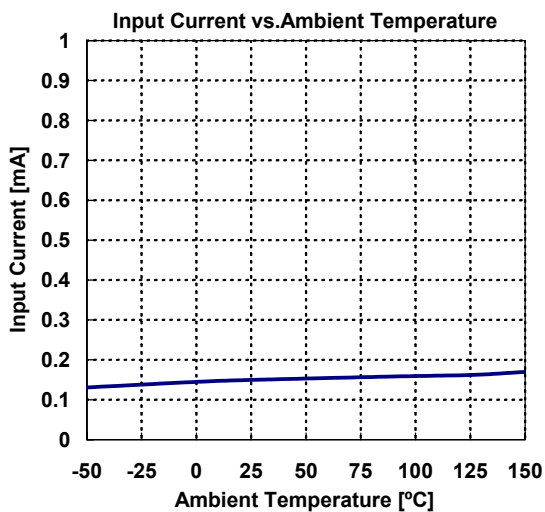
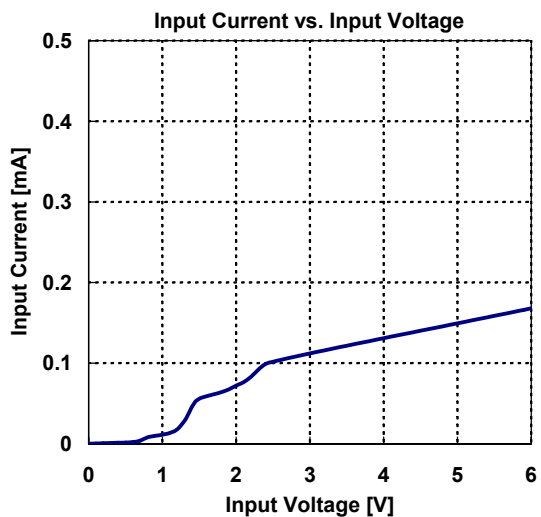
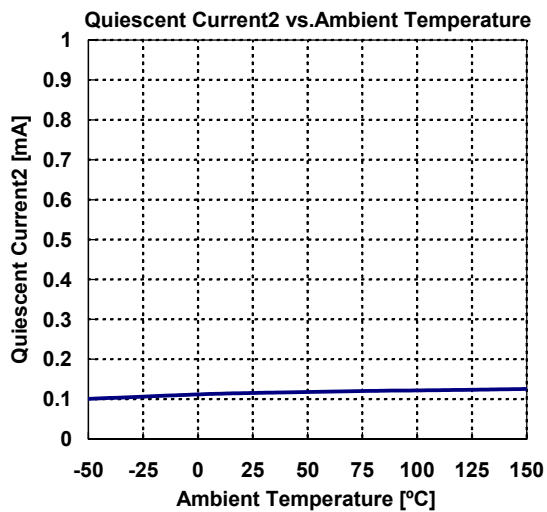
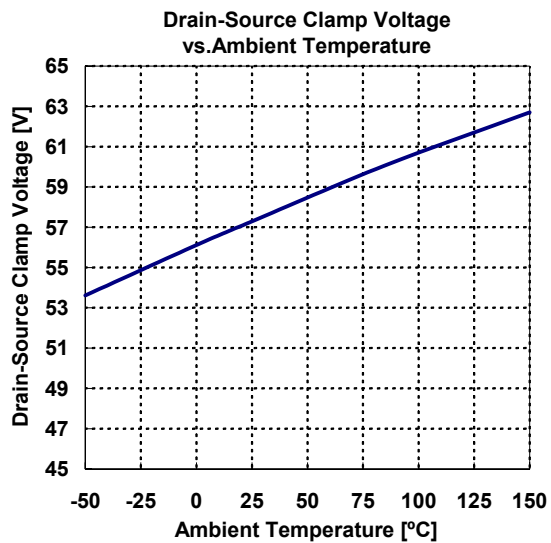
## OVER CURRENT PROTECTION CHARACTERISTIC



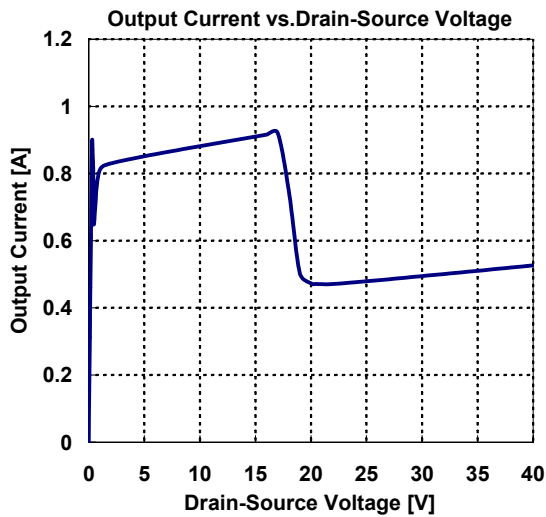
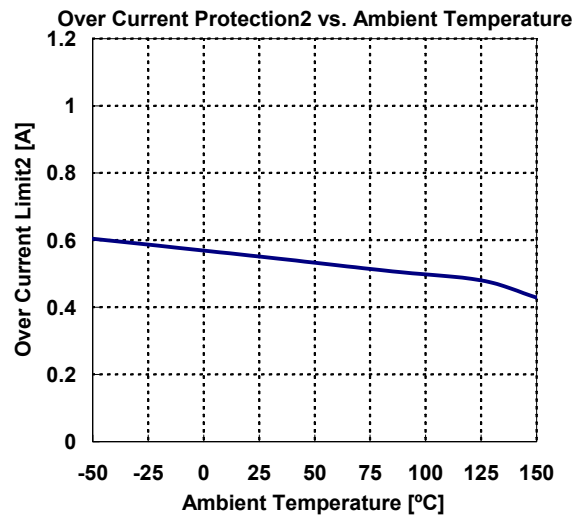
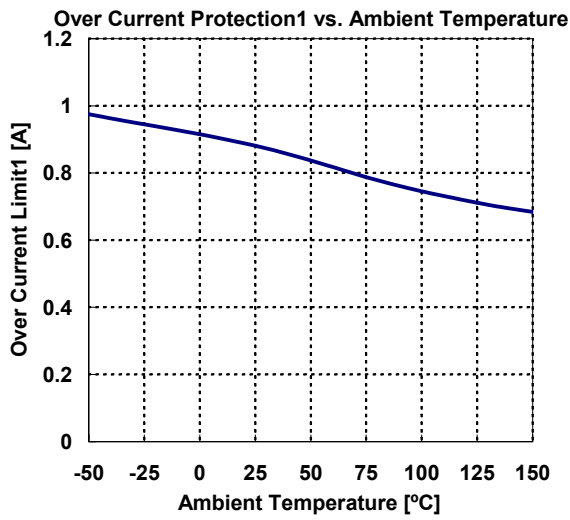
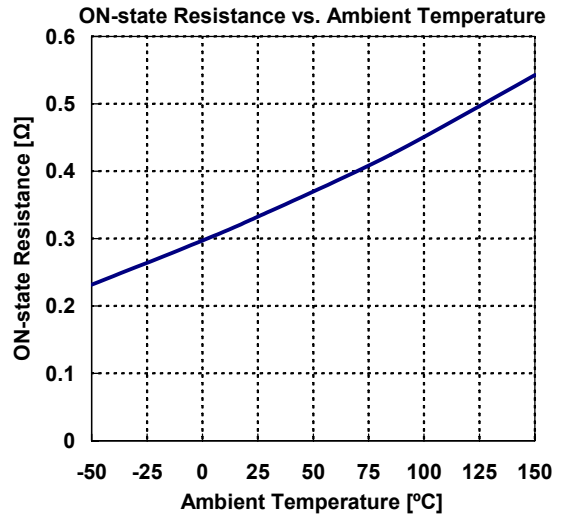
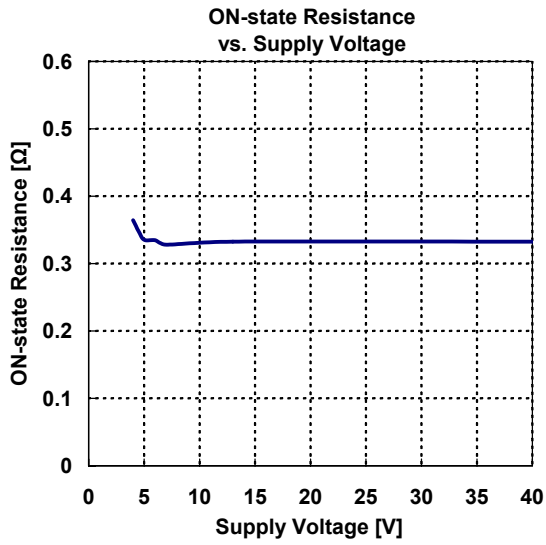
## TYPICAL APPLICATION



## ■ CHARACTERISTICS

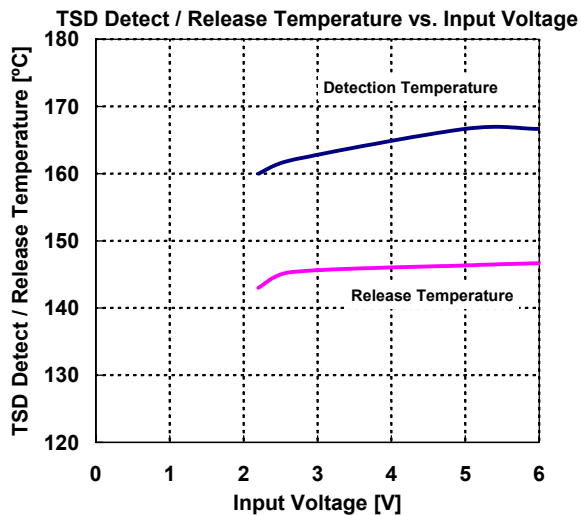
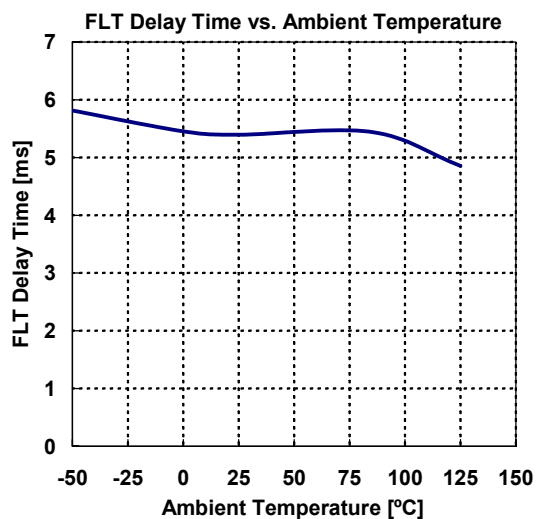
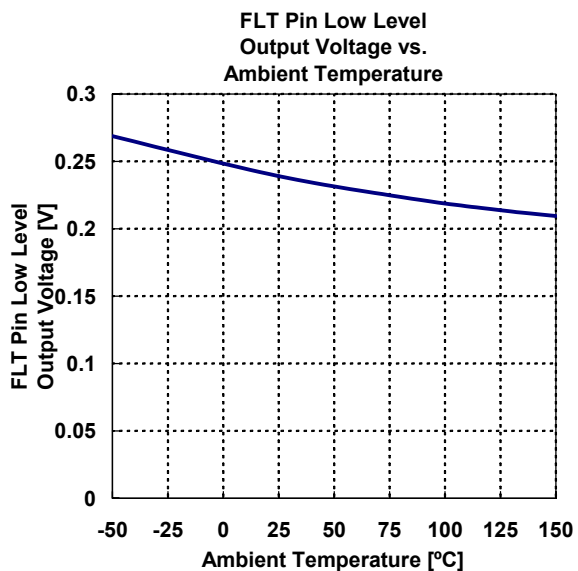
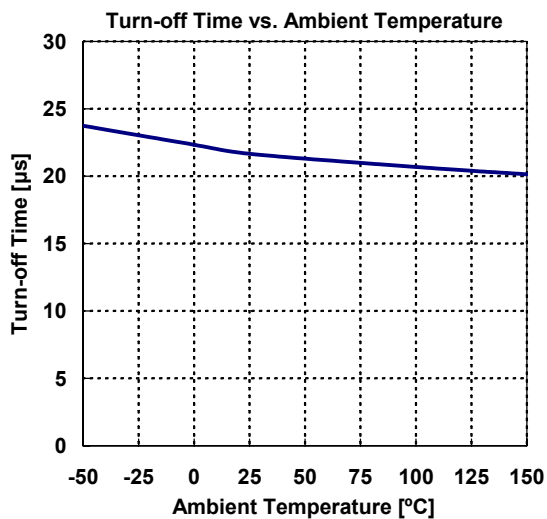
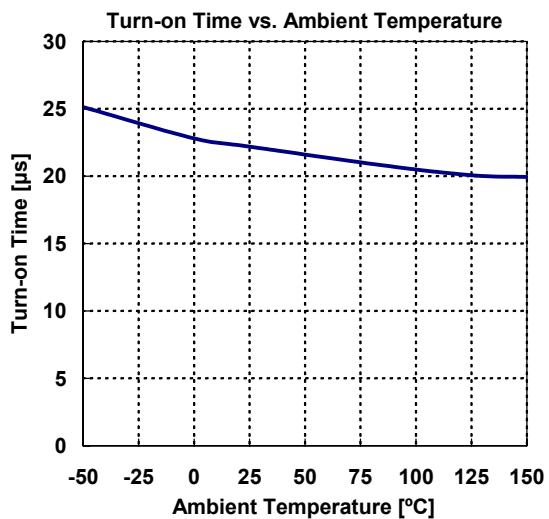


## ■ CHARACTERISTICS





## ■ CHARACTERISTICS



### ■ Regarding Active Clamp Capacity of High/Low side Switch Products

- What is "Active Clamp Capacity".

The IC might suffer to damage by the inductive kickback at the transient time of ON state to OFF state, when an inductive load such as a solenoid or motor is used for the load of the high-side/low-side switch.

The protection circuit for the inductive kickback is the active clamp circuit. The energy that can be tolerated by the active clamp circuit is called "Active Clamp Capacity ( $E_{AS}$ )".

When using an inductive load to the high-side/low-side switch, you should design so that the  $E_{SW}$  does not exceed the active clamp capability.

- IC operation without an external protection parts (Fig 1)

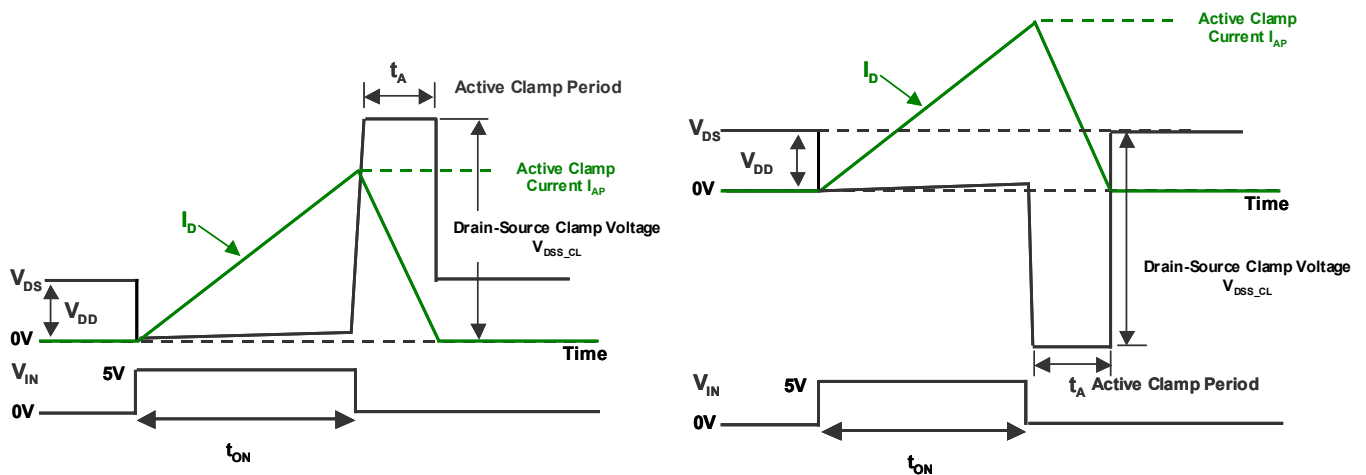


Fig1. Active Clamp Waveform (Left: Low-side Switch / Light High-side Switch)

At when the  $V_{IN}$  turns off, the drain-source voltage ( $V_{DS}$ ) increases rapidly by the behavior of the inductive load that is keeping current flowing. However, it will be clamped at  $V_{DSS\_CL}$  by the active clamp circuit. At the same time, the drain current is flowed by adjusting the gate voltage of the output transistor, and the energy is dissipated at the output transistor. The energy:  $E_{SW}$  is shown by the following formula.

$$E_{SW} = \int_0^{t_A} V_{DS}(t) \cdot I_D(t) dt = \frac{1}{2} L I_{AP}^2 \cdot \frac{V_{DSS\_CL}}{V_{DSS\_CL} - V_{DD}}$$

The  $E_{SW}$  is consumed inside IC as heat energy. However, the thermal shutdown does not work when the  $V_{IN}$  is 0V. Therefore in worst case the IC might break down. When using the active clamp, you should design  $E_{SW}$  does not exceed the  $E_{AS}$ .

- Application Hint

The simplest protection example is to add an external flywheel diode at the load to protect IC from an inductive kickback. (Fig.2)

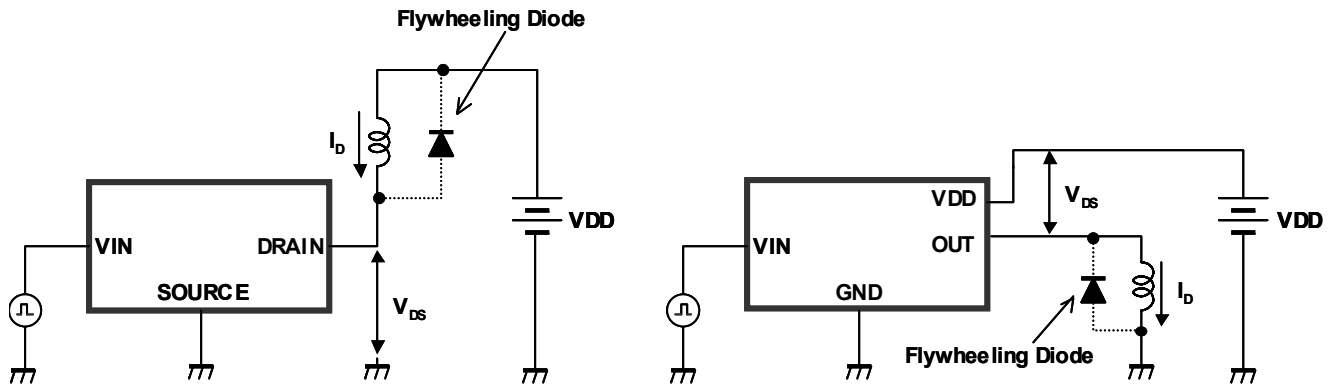


Fig 2. Application Circuit of Inductance Load Driving (Left: Low-side Switch / Light High-side Switch)

[CAUTION]

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